

TECHNICAL DATA
DATA SHEET 4123, REV. A

HERMETIC POWER SCHOTTKY RECTIFIER
Low Reverse Leakage
175 °C Operating Temperature

DESCRIPTION: 60 VOLT, 15 AMP, POWER SCHOTTKY RECTIFIER IN A TO-257 2-LEAD PACKAGE.

MAXIMUM RATINGS

ALL RATINGS ARE @ $T_C = 25\text{ }^\circ\text{C}$ UNLESS OTHERWISE SPECIFIED.

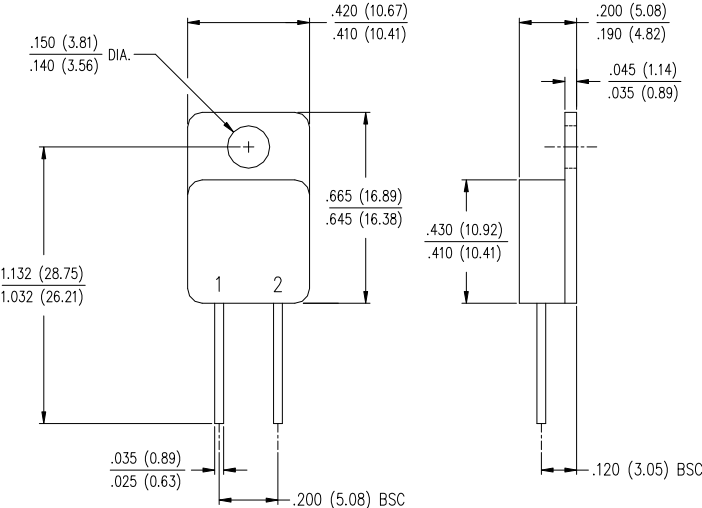
RATING	SYMBOL	MAX.	UNITS
PEAK INVERSE VOLTAGE	PIV	60	Volts
MAXIMUM DC OUTPUT CURRENT (With Cathode Maintained @ $T_C=100\text{ }^\circ\text{C}$)	I_O	15	Amps
MAXIMUM NONREPETITIVE FORWARD SURGE CURRENT ($t=8.3\text{ms}$, Sine)	I_{FSM}	280	Amps
MAXIMUM JUNCTION CAPACITANCE ($V_f=5\text{V}$)	C_T	720	pF
MAXIMUM THERMAL RESISTANCE (Junction to Mounting Surface, Cathode)	$R_{\theta JC}$	2.0	$^\circ\text{C/W}$
MAXIMUM OPERATING AND STORAGE TEMPERATURE RANGE	Top/Tstg	-65 to + 175	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS

CHARACTERISTIC			
MAXIMUM FORWARD VOLTAGE DROP, Pulsed ($I_f = 15\text{ Amps}$) $T_J = 25\text{ }^\circ\text{C}$ $T_J = 125\text{ }^\circ\text{C}$	V_f	.80 .73	Volts
MAXIMUM REVERSE CURRENT (I_r @ 60V PIV) $T_J = 25\text{ }^\circ\text{C}$ $T_J = 125\text{ }^\circ\text{C}$	I_r	0.4 30	mA

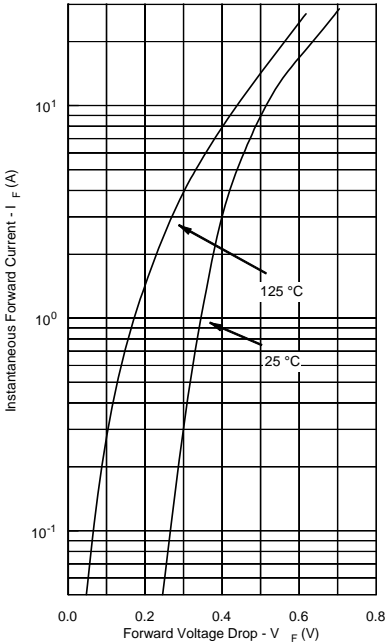
SENSITRON
DATA SHEET 4123, REV. A

MECHANICAL DIMENSIONS: In Inches / mm

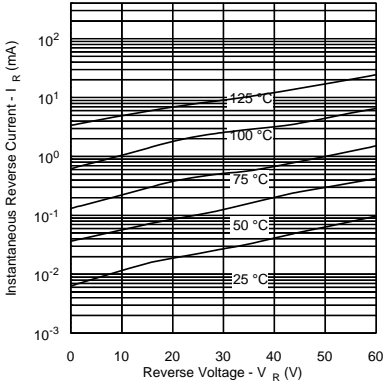


Pin 1: Cathode
Pin 2: Anode

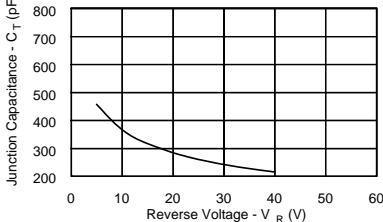
Typical Forward Characteristics



Typical Reverse Characteristics



Typical Junction Capacitance



Note: V_f curves are for bare die only.

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